

	Typ	L #	Hits	S arch T xt	DBs
1	BRS	L1	121	(deposition or depositing or deposit or deposited) near20 trisilane	USPAT; US-PG PUB
2	BRS	L3	1	2 same (simultaneous or simultaneously)	USPAT; US-PG PUB
3	BRS	L2	18	1 same (germanium or ge)	USPAT; US-PG PUB
4	BRS	L4	27	(deposition or depositing or deposit or deposited) near20 trisilane	EPO; JPO; DERWE NT; IBM_TD B
5	BRS	L5	5	4 and (germanium or ge)	EPO; JPO; DERWE NT; IBM_TD B
6	BRS	L6	4604	(monocrystal or (single adj crystalline)) same (amorphous or polycrystalline or polysilicon)	USPAT; US-PG PUB
7	BRS	L7	1012	6 same (deposit or depositing or deposition)	USPAT; US-PG PUB
8	BRS	L8	3114	(monocrystal or (single adj crystalline)) near20 (amorphous or polycrystalline or polysilicon)	USPAT; US-PG PUB
9	BRS	L9	250	8 near20 (deposit or depositing or deposition)	USPAT; US-PG PUB
10	BRS	L10	900	(monocrystal or (single adj crystalline)) near2 (surfaces or surface)	USPAT; US-PG PUB
11	BRS	L11	5788	(amorphous or polycrystalline or polysilicon) adj2 (surfaces or surface)	USPAT; US-PG PUB
12	BRS	L12	20	10 same 11	USPAT; US-PG PUB